L	Hits	Search Text	DB	Time stamp
Number				_
-	69	polysilicon same silicon adj tetrachloride	USPAT	2004/10/20 13:04
-	20	,	US-PGPUB;	2004/10/19
		tetrachloride	EPO; JPO; DERWENT; IBM TDB	16:45
_	721	high adj k adj dielectric same gate	USPAT;	2004/10/19
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	16:46
-	592	high adj k adj dielectric with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/19
-	288	high adj k adj dielectric with gate	USPAT	2004/10/19
-	18	polysilicon near2 gate with (ald or pvd)	USPAT	2004/10/20
-	401	polysilicon with (ald or pvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/20
-	43	polysilicon with silicon adj tetrachloride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/20 09:43
_	4	polysilicon same high adj k nearl dielectric same hydrogen near2 free	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/20 10:21